



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

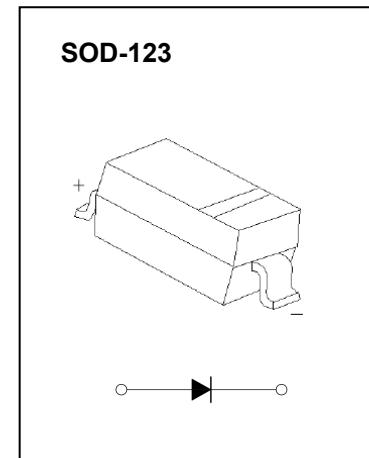
SOD-123 Plastic-Encapsulate Diodes

SD101AW

SCHOTTKY BARRIER DIODE

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time



MARKING: S1

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Value			Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	60			V
Working Peak Reverse Voltage	V_{RWM}	60			V
DC Blocking Voltage	V_R	60			V
RMS Reverse Voltage	$V_{R(RMS)}$	42			V
Forward Continuous Current	I_{FM}	15			mA
Repetitive Peak Forward Current @t<1.0s @t=10μs	I_{FRM}	50 2.0			mA A
Power Dissipation	P_d	400			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	250			°C/W
Junction temperature	T_j	125			°C
Storage Temperature	T_{STG}	-55~+150			°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	60			V	$IR=10\mu A$
Forward voltage	V_F			0.41 1.00	V	$I_F=1.0mA$ $I_F=15mA$
Reverse current	I_{RM}			0.2	μA	$V_R=50V$
Capacitance between terminals	C_T			2.0	pF	$V_R=0V, f=1.0MHz$
Reverse recovery time	t_{rr}			1. 0	ns	$I_F=I_R=5mA$ $I_{rr}=0.1XI_R, R_L=100\Omega$

Typical Characteristics

SD101AW

